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(54) **Title:** PLASMA HYPERMODEL INTEGRATED WITH FEATURE-SCALE PROFILE MODEL FOR ACCELERATED ETCH PROCESS DEVELOPMENT

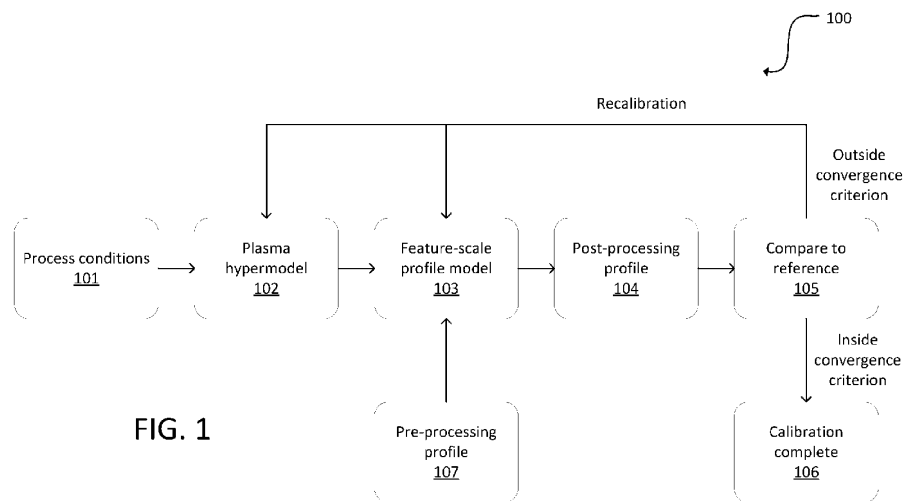


FIG. 1

(57) **Abstract:** Plasma parameters at a surface of a wafer are determined with a plasma hypermodel based on plasma processing conditions. A post-processing profile can be predicted for the surface of the wafer with a feature-scale profile model. Correlations in the plasma hypermodel can be recalibrated if the post-processing profile is outside a convergence criterion of an experimental reference.